SWITCHMODE NPN Silicon Power Transistors

The BUX85G is designed for high voltage, high speed power switching applications like converters, inverters, switching regulators, motor control systems.

Features

• These Devices are Pb-Free and are RoHS Compliant*

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Collector-Emitter Voltage	V _{CEO(sus)}	450	Vdc
Collector-Emitter Voltage	V _{CES}	1000	Vdc
Emitter-Base Voltage	V _{EBO}	5	Vdc
Collector Current – Continuous	۱ _C	2	Adc
Collector Current – Peak (Note 1)	I _{CM}	3.0	Adc
Base Current – Continuous	Ι _Β	0.75	Adc
Base Current – Peak (Note 1)	I _{BM}	1.0	Adc
Reverse Base Current - Peak	I _{BM}	1	Adc
Total Device Dissipation @ $T_C = 25 \degree C$ Derate above $25 \degree C$	PD	50 400	W W/°C
Operating and Storage Junction Temperature Range	T _J , T _{stg}	-65 to +150	°C

THERMAL CHARACTERISTICS

Characteristics	Symbol	Max	Unit
Thermal Resistance, Junction-to-Case	$R_{\theta JC}$	2.5	°C/W
Thermal Resistance, Junction-to-Ambient	$R_{\theta JA}$	62.5	°C/W
Maximum Lead Temperature for Soldering Purposes 1/8" from Case for 5 Seconds	ΤL	275	°C

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

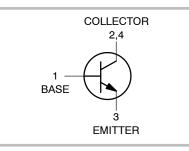
1. Pulse Test: Pulse Width = 5 ms, Duty Cycle $\leq 10\%$.

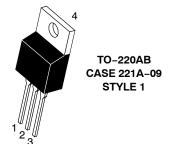


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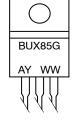
http://onsemi.com

2.0 AMPERES **POWER TRANSISTOR** NPN SILICON **450 VOLTS, 50 WATTS**





MARKING DIAGRAM



BUX85 = Device Code A

= Assembly Location = Year

= Work Week

Y

ww = Pb-Free Package G

ORDERING INFORMATION

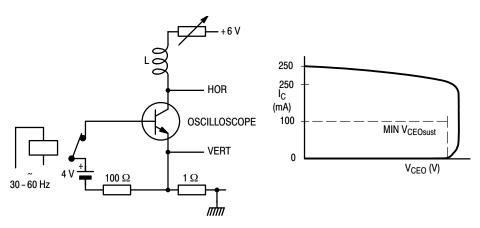
Device	Package	Shipping
BUX85G	TO-220 (Pb-Free)	50 Units / Rail

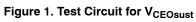
*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

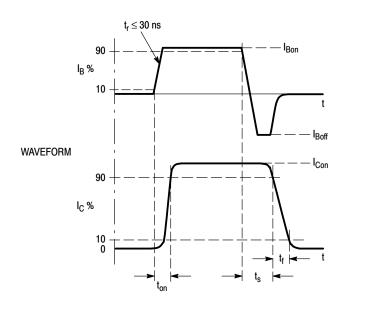
ELECTRICAL CHARACTERISTICS (T_C = 25° C unless otherwise noted)

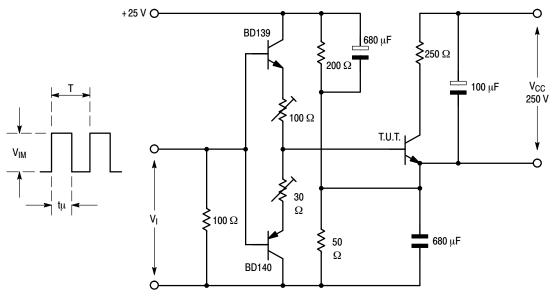
	Symbol	Min	Тур	Max	Unit	
OFF CHARACTERIST	ICS (Note 2)					
Collector–Emitter Sustaining Voltage (I _C = 100 mAdc, (L = 25 mH) See Figure 1		V _{CEO(sus)}	450	-	-	Vdc
Collector Cutoff Current (V _{CES} = Rated Value) (V _{CES} = Rated Value, T _C = 125°C)		ICES			0.2 1.5	mAdc
Emitter Cutoff Current (V _{EB} = 5 Vdc, I _C = 0	I _{EBO}	_	_	1	mAdc	
ON CHARACTERISTIC	CS (Note 2)					
DC Current Gain (I _C = 0.1 Adc, V _{CE} = 5 V)		h _{FE}	30	50	_	-
Collector-Emitter Saturation Voltage ($I_C = 0.3 \text{ Adc}, I_B = 30 \text{ mAdc}$) ($I_C = 1 \text{ Adc}, I_B = 200 \text{ mAdc}$)		V _{CE(sat)}			0.8 1	Vdc
Base-Emitter Saturation Voltage $(I_{C} = 1 \text{ Adc}, I_{B} = 0.2 \text{ Adc})$		V _{BE(sat)}	_	-	1.1	Vdc
DYNAMIC CHARACTE	ERISTICS					
Current–Gain – Bandwidth Product (I _C = 500 mAdc, V _{CE} = 1 0 Vdc, f = 1 MHz)		f _T	4	-	_	MHz
SWITCHING CHARAC	TERISTICS			•		•
Turn-on Time	V _{CC} = 250 Vdc, I _C = 1 A	t _{on}	-	0.3	0.5	μs
Storage Time	$I_{B1} = 0.2 \text{ A}, I_{B2} = 0.4 \text{ A}$	t _s	-	2	3.5	μs
Fall Time	See Figure 2	t _f	-	0.3	-	μs
Fall Time	Same above cond. at $T_C = 95^{\circ}C$		-	-	1.4	μs

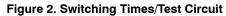
2. Pulse Test: PW = 300 μ s, Duty Cycle \leq 2%.





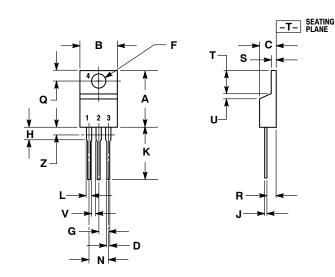






PACKAGE DIMENSIONS

TO-220 CASE 221A-09 **ISSUE AG**



NOTES

3

DIMENSIONING AND TOLERANCING PER ANSI 1. Y14.5M, 1982. CONTROLLING DIMENSION: INCH. 2

DIMENSION Z DEFINES A ZONE WHERE ALL BODY AND LEAD IRREGULARITIES ARE ALLOWED.

	INCHES		HES MILLIMETERS		
DIM	MIN	MAX	MIN MAX		
Α	0.570	0.620	14.48	15.75	
В	0.380	0.405	9.66	10.28	
С	0.160	0.190	4.07	4.82	
D	0.025	0.036	0.64	0.91	
F	0.142	0.161	3.61	4.09	
G	0.095	0.105	2.42	2.66	
Н	0.110	0.161	2.80	4.10	
J	0.014	0.025	0.36	0.64	
Κ	0.500	0.562	12.70	14.27	
L	0.045	0.060	1.15	1.52	
Ν	0.190	0.210	4.83	5.33	
Q	0.100	0.120	2.54	3.04	
R	0.080	0.110	2.04	2.79	
S	0.045	0.055	1.15	1.39	
Т	0.235	0.255	5.97	6.47	
U	0.000	0.050	0.00	1.27	
۷	0.045		1.15		
Ζ		0.080		2.04	

STYLE 1: PIN 1.

BASE COLLECTOR 2

EMITTER 3. COLLECTOR 4.

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